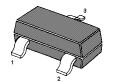
BC807 / BC808-AH

PNP Silicon Epitaxial Planar Transistors

Features

- AEC-Q101 Qualified
- These transistors are subdivided into three groups -16, -25 and -40, according to their current gain.
 As complementary types the NPN transistors BC817 and BC818 are recommended.
- Halogen and Antimony Free(HAF), RoHS compliant



1.Base 2.Emitter 3.Collector SOT-23 Plastic Package

Applications

· For switching, AF driver and amplifier applications

Absolute Maximum Ratings (T_a = 25°C)

Parameter	Symbol	Value	Unit	
Collector Base Voltage	BC807 BC808	-V _{CBO}	50 30	V
Collector Emitter Voltage	BC807 BC808	-Vceo	45 25	V
Emitter Base Voltage		-V _{EBO}	5	V
Collector Current		-lc	500	mA
Total Power Dissipation 1)		P _{tot}	300	mW
Junction Temperature		Tj	150	°C
Storage Temperature Range		T_{stg}	- 55 to + 150	°C

Thermal Characteristics

Parameter	Symbol	Max.	Unit
Thermal Resistance from Junction to Ambient 1)	Reja	417	°C/W

¹⁾Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.



BC807 / BC808-AH

Electrical Characteristics at T_a = 25°C

Parameter	Symbol	Min.	Тур.	Max.	Unit	
DC Current Gain at -V _{CE} = 1 V, -I _C = 100 mA	-16 -25 -40	hfe hfe hfe	100 160 250	- - -	250 400 600	- - -
at -V _{CE} = 1 V, -I _C = 500 mA Collector Base Cutoff Current at -V _{CB} = 20 V		h _{FE}	40 -	-	100	nA
Emitter Base Cutoff Current at -V _{EB} = 5 V		-I _{EBO}	-	-	100	nA
Collector Base Breakdown Voltage at -l _C = 10 μA	BC807 BC808	-V _{(BR)CBO}	50 30	-	-	V
Collector Emitter Breakdown Voltage at $-I_C = 10$ mA	BC807 BC808	-V _{(BR)CEO}	45 25	-	-	V
Emitter Base Breakdown Voltage at -l _E = 10 μA		-V _{(BR)EBO}	5	-	-	V
Collector Emitter Saturation Voltage at $-I_C = 500$ mA, $-I_B = 50$ mA		-V _{CE(sat)}	-	-	0.7	V
Base Emitter On Voltage at -l _C = 500 mA, -V _{CE} = 1 V		-V _{BE(on)}	-	-	1.2	V
Transition Frequency at -V _{CE} = 5 V, -I _C = 10 mA, f = 50 MHz		f⊤	80	-	-	MHz
Collector Output Capacitance at -V _{CB} = 10 V, f = 1 MHz		Cob	-	9	-	pF



Electrical Characteristics Curves

Fig. 1 Output Characteristics Curve

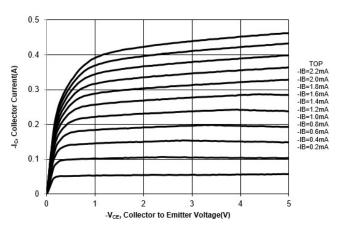


Fig. 2 Collector Current vs. Base to Emitter

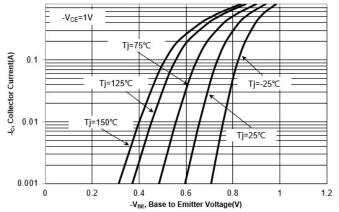


Fig. 3 DC Current Gain vs. Collector Current

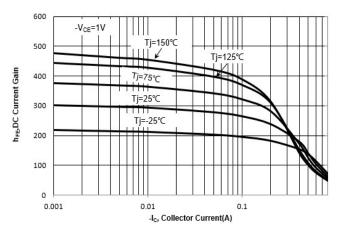
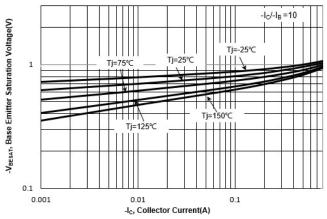


Fig. 4 V_{BESAT} vs. Collector Current





Electrical Characteristics Curves

Fig. 5 V_{CESAT} vs. Collector Current

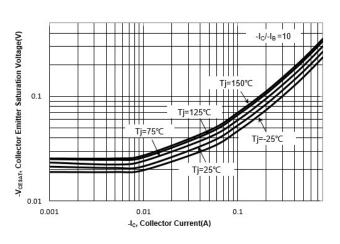


Fig. 6 Output Capacitance

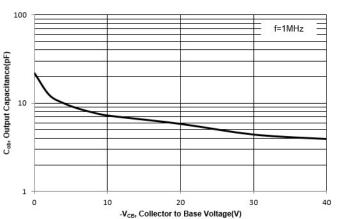
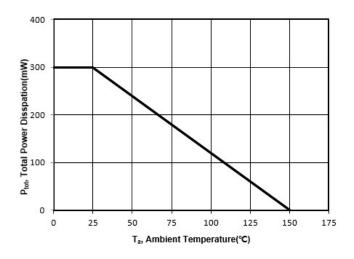


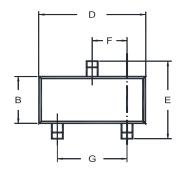
Fig 7. Power Derating Curve

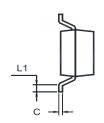


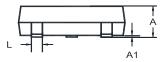


Package Outline (Dimensions in mm)

SOT-23

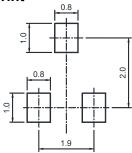






Unit	Α	A1	В	С	D	E	F	G	L	L1
	1.20	0.100	1.40	0.19	3.04	2.6	1.02	2.04	0.51	0.2
mm	0.89	0.013	1.20	0.08	2.80	2.2	0.89	1.78	0.37	MIN

Recommended Soldering Footprint

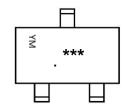


Packing information

	Tape Width	Pitch		Reel	Size	Per Reel Packing Quantity	
Package (mm)		mm	inch	mm	inch		
SOT-23	8	4 ± 0.1	0.157 ± 0.004	178	7	3,000	

Marking information

Part No.	Marking Code
BC807-16&BC808-16	5CR
BC807-25&BC808-25	5CS
BC807-40&BC808-40	5CT



Font type: Arial

Disclaimer: Our company reserve the right to make modifications, enhancements, improvements, corrections or other changes to improve product design, functions and reliability, anytime without notice. Semtech Electronics Limited makes no warranties, representations or warranties regarding the suitability of its products for any particular purpose, and does not accept any liability arising from the application or use of any product or circuit such as: Apply to medical, military, aircraft, space or life support equipment and expressly waive any and all liability, including but not limited to special, consequential or collateral damage.



[&]quot;•" = HAF (Halogen and Antimony Free)

[&]quot; YM " = Date Code Marking

[&]quot; Y " = Year

[&]quot; M " = Month